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ELEMENT AND FABRICATION METHOD
THEREFOR, AND SEMICONDUCTOR
IMAGE SENSING DEVICE AND
FABRICATION METHOD THEREFOR****Publication Classification**(51) **Int. Cl.**
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Kiyokazu Itoi, Osaka (JP); **Toshiyuki
Fukuda**, Kyoto (JP)(57) **ABSTRACT**Correspondence Address:
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A semiconductor image sensing element has a semiconductor element including an image sensing area, a peripheral circuit region, a plurality of electrode portions provided in the peripheral circuit region, and a plurality of micro-lenses provided on the image sensing area and an optical member having a configuration covering at least the image sensing area and bonded over the micro-lenses via a transparent bonding member. The side surface region of the optical member is formed with a light shielding film for preventing the irradiation of the image sensing area with a reflected light beam or a scattered light beam from the side surface region.

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